

PSMN7R0-60YS

N-channel LFPAK 60 V 6.4 m Ω standard level MOSFET

Rev. 02 — 30 March 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	60	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	89	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	117	W
Tj	junction temperature		-55	-	175	°C
Avalanci	he ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 89.1 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω; unclamped	-	-	143	mJ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 60 \text{ A};$	-	9.6	-	nC
$Q_{G(tot)} \\$	total gate charge	V _{DS} = 30 V; see <u>Figure 14</u> and <u>15</u>	-	45	-	nC



Table 1. Quick reference ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{}$	-	-	10.2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$	-	4.95	6.4	mΩ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb (D
3	S	source		
4	G	gate	Q	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 Ś
			SOT669 (LFPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN7R0-60YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	60	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	60	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	63	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	-	89	Α
I _{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	356	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	117	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-di	ain diode				
Is	source current	$T_{mb} = 25 ^{\circ}C$	-	89	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	356	Α
Avalanch	e ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 89.1 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω; unclamped	-	143	mJ

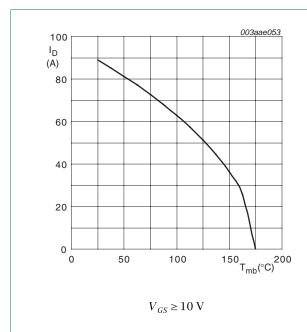


Fig 1. Continuous drain current as a function of mounting base temperature

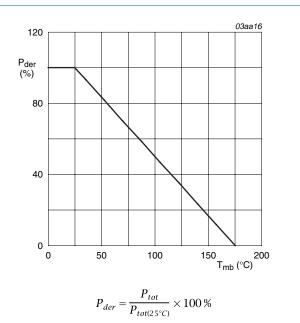
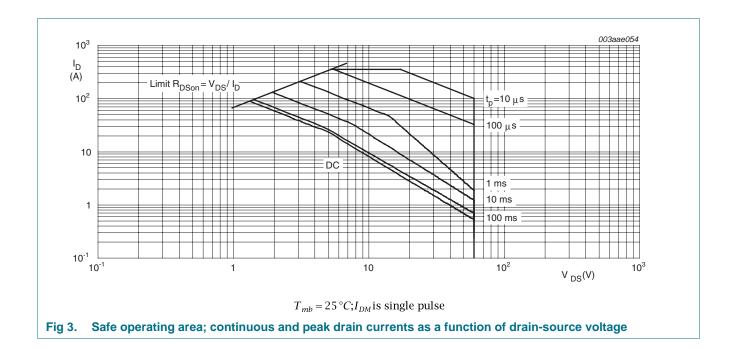


Fig 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.54	1.28	K/W

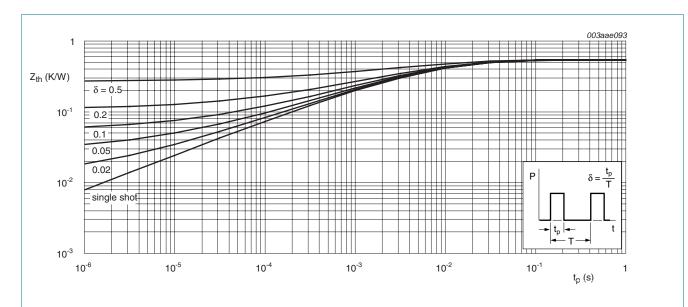


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 10</u> and <u>11</u>	2	3	4	V
V_{GSth}		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 11	-	-	4.7	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{\text{ or } 11}$	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.04	2	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon} drain-source on-state	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 12}{}$	-	9.3	14.7	mΩ
	resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	10.2	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	4.95	6.4	mΩ
R_G	gate resistance	f = 1 MHz	-	0.65	1.5	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	I_D = 60 A; V_{DS} = 30 V; V_{GS} = 10 V; see <u>Figure 14</u> and <u>15</u>	-	45	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	37.6	-	nC
Q _{GS}	gate-source charge	$I_D = 60 \text{ A}$; $V_{DS} = 30 \text{ V}$; $V_{GS} = 10 \text{ V}$; see <u>Figure 14</u>		14.8	-	nC
Q _{GS(th)}	pre-threshold gate-source charge			7.9	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	6.8	-	nC
Q_{GD}	gate-drain charge	I_D = 60 A; V_{DS} = 30 V; V_{GS} = 10 V; see <u>Figure 14</u> and <u>15</u>	-	9.6	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 30 \text{ V}$; see Figure 14 and 15	-	4.9	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_i = 25 °C;$	-	2712	-	pF
C _{oss}	output capacitance	see Figure 16	-	366	-	pF
C _{rss}	reverse transfer capacitance		-	202	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 10 \text{ V};$	-	19.9	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	20.3	-	ns
t _{d(off)}	turn-off delay time		-	37.9	-	ns
t _f	fall time		-	12.6	-	ns
•	ain diode					
V_{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _i = 25 °C; see Figure 17	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; \text{ dI}_S/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	_	41.9	-	ns
Q _r	recovered charge	$V_{DS} = 30 \text{ V}$	_	57.3	-	nC
∽ r	. 500 voi ou onargo			07.0		0

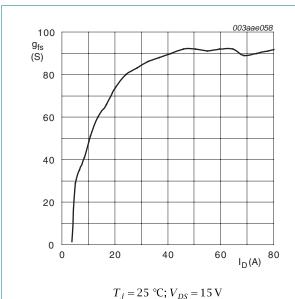


Fig 5. Forward transconductance as a function of drain current; typical values

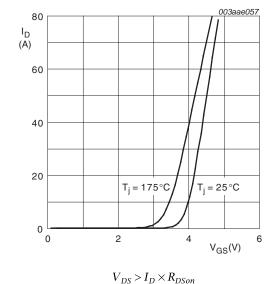


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

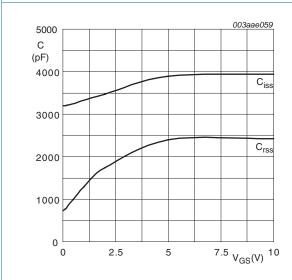


Fig 7. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

 $V_{GS} = 0 \text{ V; } f = 1 \text{ MHz}$

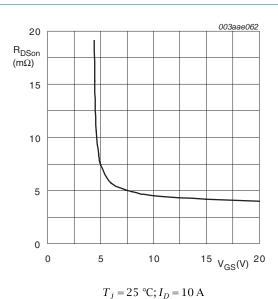


Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

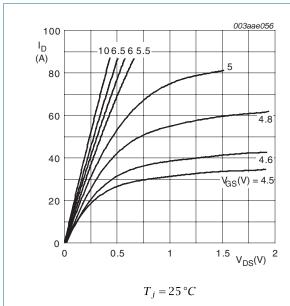


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

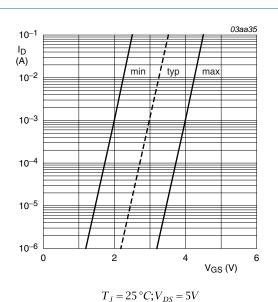


Fig 10. Sub-threshold drain current as a function of gate-source voltage

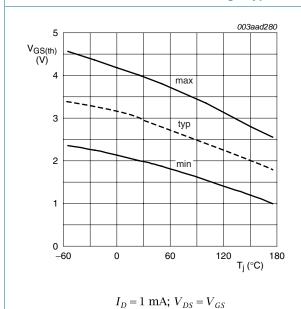
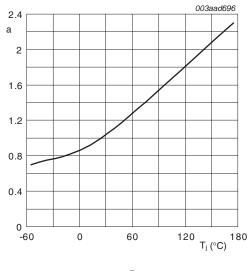


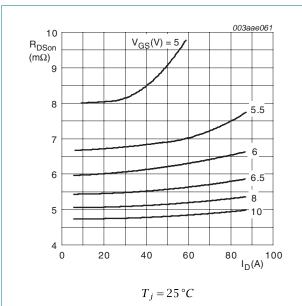
Fig 11. Gate-source threshold voltage as a function of

junction temperature



 $a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$

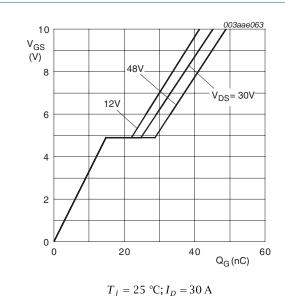
Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature.



V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_G(tot)
003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

Fig 14. Gate charge waveform definitions



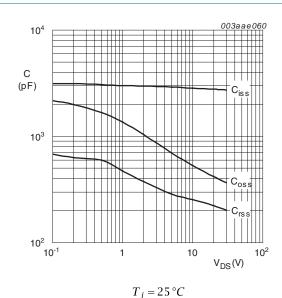
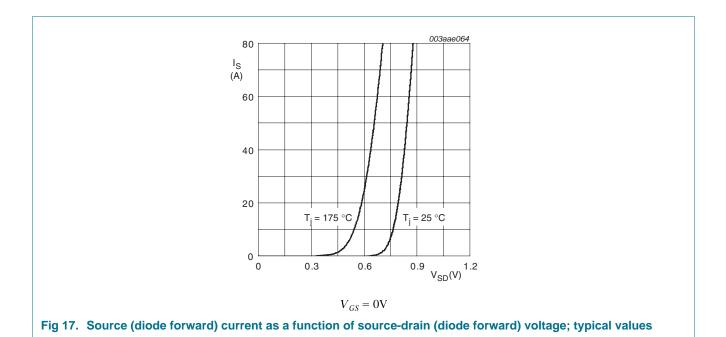


Fig 15. Gate-source voltage as a function of gate charge; typical values

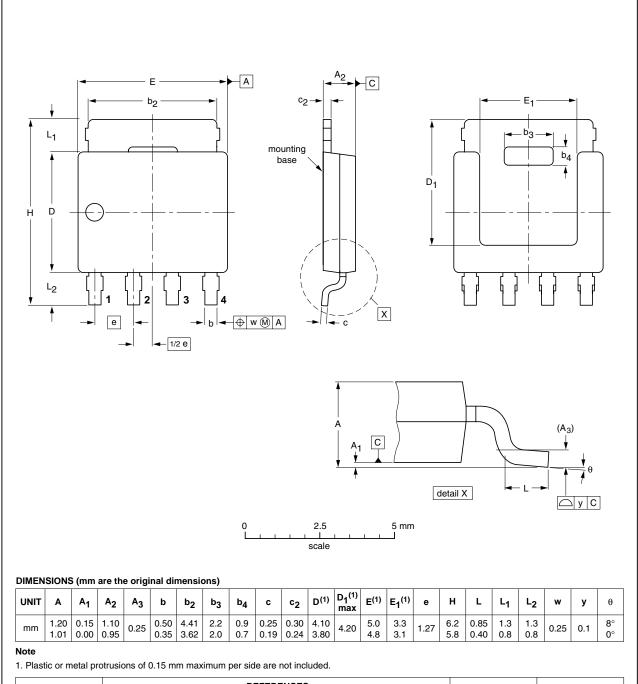
Fig 16. Drain-source on-state resistance as a function of drain current; typical values



7. Package outline

Plastic single-ended surface-mounted package (LFPAK); 4 leads

SOT669



OUTLINE		REFER	ENCES	EUROPEAN ISSUE D		
VERSION	IEC	C JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT669		MO-235			04-10-13 06-03-16	

Fig 18. Package outline SOT669 (LFPAK)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN7R0-60YS_2	20100330	Product data sheet	-	PSMN7R0-60YS_1
Modifications:		nged from objective to pa anges to content.	oduct.	
PSMN7R0-60YS_1	20100112	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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